MAXIMUM RATINGS ($T_A = +25^{\circ}C$, unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage (-5 V) (-12, -15, -18 V) (-24 V)	V _I	-30 -35 -40	Vdc
Power Dissipation Case 29 (TO-92 Type) T _A = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case Case 751 (SOIC-8 Type) (Note 1) T _A = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	PD R ₀ JA R ₀ JC PD R ₀ JA R ₀ JC	Internally Limited 160 83 Internally Limited 180 45	W °C/W °C/W °C/W °C/W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Human Body Model 2000 V per MIL_STD_883, Method 3015

Machine Model Method 200 V.

ELECTRICAL CHARACTERISTICS (V_I = -10 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L05AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage $(T_J = +25^{\circ}C)$	V _O	-4.8	-5.0	-5.2	Vdc
Input Regulation ($T_J = +25^{\circ}C$) $-7.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$ $-8.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$	Reg _{line}	- -	- -	150 100	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA}$ $1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	-	- -	60 30	mV
Output Voltage $ -7.0 \text{ Vdc} \geq V_I \geq -20 \text{ Vdc}, \ 1.0 \text{ mA} \leq I_O \leq 40 \text{ mA} $ $V_I = -10 \text{ Vdc}, \ 1.0 \text{ mA} \leq I_O \leq 70 \text{ mA} $	V _O	-4.75 -4.75	- -	-5.25 -5.25	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.0 5.5	mA
Input Bias Current Change $-8.0 \text{ Vdc} \ge \text{V}_{\text{I}} \ge -20 \text{ Vdc}$ $1.0 \text{ mA} \le \text{I}_{\text{O}} \le 40 \text{ mA}$	I _{IB}	- -	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	-	40	-	μV
Ripple Rejection ($-8.0 \ge V_I \ge -18 \text{ Vdc}$, f = 120 Hz, $T_J = +25^{\circ}\text{C}$)	RR	41	49	-	dB
Dropout Voltage (I _O = 40 mA, T _J = +25°C)	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} SOIC-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 9 for Thermal Resistance variation versus pad size.

^{*}This device series contains ESD protection and exceeds the following tests:

ELECTRICAL CHARACTERISTICS (V_I = -19 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L12AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	V _O	-11.5	-12	-12.5	Vdc
Input Regulation (T_J = +25°C) -14.5 Vdc \geq V $_I$ \geq -27 Vdc -16 Vdc \geq V $_I$ \geq -27 Vdc	Reg _{line}	- -	- -	250 200	mV
Load Regulation $T_J = +25^{\circ}\text{C}, \ 1.0 \ \text{mA} \leq I_O \leq 100 \ \text{mA} \\ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA}$	Reg _{load}	- -	-	100 50	mV
Output Voltage $-14.5 \text{ Vdc} \ge V_l \ge -27 \text{ Vdc, } 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ V_l = -19 \text{ Vdc, } 1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-11.4 -11.4	-	-12.6 -12.6	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.5 6.0	mA
Input Bias Current Change -16 Vdc \geq V _I \geq -27 Vdc 1.0 mA \leq I _O \leq 40 mA	I _{IB}	- -	- -	1.5 0.2	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz $\leq f \leq$ 100 kHz)	V _n	-	80	-	μV
Ripple Rejection ($-15 \le V_1 \le -25 \text{ Vdc}$, f = 120 Hz, T _J = $+25^{\circ}\text{C}$)	RR	37	42	-	dB
Dropout Voltage (I _O = 40 mA, T _J = +25°C)	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -23 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		M	C79L15AC, A	AB	
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage (T _J = +25°C)	V _O	-14.4	-15	-15.6	Vdc
Input Regulation ($T_J = +25^{\circ}C$) -17.5 Vdc $\geq V_I \geq -30$ Vdc -20 Vdc $\geq V_I \geq -30$ Vdc	Reg _{line}	- -	- -	300 250	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \ mA \leq I_O \leq 100 \ mA \\ 1.0 \ mA \leq I_O \leq 40 \ mA$	Reg _{load}	- -	- -	150 75	mV
Output Voltage $-17.5 \text{ Vdc} \ge V_l \ge -\text{Vdc}, \ 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ V_l = -23 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-14.25 -14.25	- -	-15.75 -15.75	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.5 6.0	mA
Input Bias Current Change -20 Vdc \geq V _I \geq -30 Vdc 1.0 mA \leq I _O \leq 40 mA	ΔI_{IB}	- -	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _N	-	90	-	μV
Ripple Rejection ($-18.5 \le V_1 \le -28.5 \text{ Vdc}$, f = 120 Hz)	RR	34	39	-	dB
Dropout Voltage I _O = 40 mA, T _J = +25°C	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -27 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC), unless otherwise noted).

			MC79L18AC	;	
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage $(T_J = +25^{\circ}C)$	V _O	-17.3	-18	-18.7	Vdc
Input Regulation ($T_J = +25^{\circ}C$) $-20.7 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-21.4 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-22 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-21 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$	Reg _{line}	- - - -	- - - -	325 - - 275	mV
Load Regulation $T_J = +25^{\circ}\text{C}, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA} \\ 1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	- -		170 85	mV
Output Voltage $ -20.7 \text{ Vdc} \ge V_l \ge -33 \text{ Vdc, } 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ -21.4 \text{ Vdc} \ge V_l \ge -33 \text{ Vdc, } 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ V_l = -27 \text{ Vdc, } 1.0 \text{ mA} \le I_O \le 70 \text{ mA} $	Vo	-17.1 - -17.1	- - -	-18.9 - -18.9	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.5 6.0	mA
Input Bias Current Change $ -21 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	I _{IB}	- - -	- - -	1.5 _ 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	_	150	_	μV
Ripple Rejection ($-23 \le V_I \le -33$ Vdc, f = 120 Hz, $T_J = +25^{\circ}C$)	RR	33	48	_	dB
Dropout Voltage I _O = 40 mA, T _J = +25°C	V _I -V _O	_	1.7	_	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -33 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC), unless otherwise noted).

		MC79L24AC			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-23	-24	-25	Vdc
Input Regulation (T_J = +25°C) -27 Vdc \geq V $_I$ \geq -38 Vdc -27.5 Vdc \geq V $_I$ \geq -38 Vdc -28 Vdc \geq V $_I$ \geq -38 Vdc	Reg _{line}	- - -	- - -	350 - 300	mV
Load Regulation $T_J = +25^{\circ}\text{C}, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA}$ $1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	- -	- -	200 100	mV
$ \begin{array}{l} \text{Output Voltage} \\ -27 \text{ Vdc} \geq V_I \geq -38 \text{ V, } 1.0 \text{ mA} \leq I_O \leq 40 \text{ mA} \\ -28 \text{ Vdc} \geq V_I \geq -38 \text{ Vdc, } 1.0 \text{ mA} \leq I_O \leq 40 \text{ mA} \\ V_I = -33 \text{ Vdc, } 1.0 \text{ mA} \leq I_O \leq 70 \text{ mA} \end{array} $	Vo	-22.8 - -22.8	- - -	-25.2 - -25.2	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}		- -	6.5 6.0	mA
Input Bias Current Change -28 Vdc \geq V $_{I}$ \geq -38 Vdc 1.0 mA \leq I $_{O}$ \leq 40 mA	Δl_{IB}	- -	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz $\leq f \leq$ 100 kHz)	V _n	-	200	-	μV
Ripple Rejection ($-29 \le V_1 \le -35 \text{ Vdc}$, f = 120 Hz, $T_J = +25^{\circ}\text{C}$)	RR	31	47	-	dB
Dropout Voltage $I_O = 40$ mA, $T_J = +25^{\circ}C$	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

APPLICATIONS INFORMATION

Design Considerations

The MC79L00A Series of fixed voltage regulators are designed with Thermal Overload Protections that shuts down the circuit when subjected to an excessive power overload condition, Internal Short Circuit Protection that limits the maximum current the circuit will pass.

In many low current applications, compensation capacitors are not required. However, it is recommended that the regulator input be bypassed with a capacitor if the regulator is connected to the power supply filter with long wire length, or if the output load capacitance is large. An input bypass capacitor should be selected to provide good

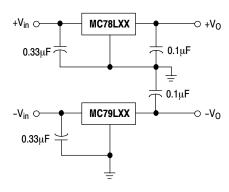
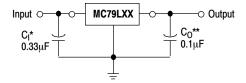


Figure 2. Positive and Negative Regulator

high–frequency characteristics to insure stable operation under all load conditions. A 0.33 μF or larger tantalum, mylar, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with the shortest possible leads directly across the regulator's input terminals. Normally good construction techniques should be used to minimize ground loops and lead resistance drops since the regulator has no external sense lead. Bypassing the output is also recommended.



A common ground is required between the input and the output voltages. The input voltage must remain typically 2.0 V above the output voltage even during the low point on the ripple voltage.

- * C_I is required if regulator is located an appreciable distance from the power supply filter
- ** Co improves stability and transient response.

Figure 3. Standard Application

TYPICAL CHARACTERISTICS

 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

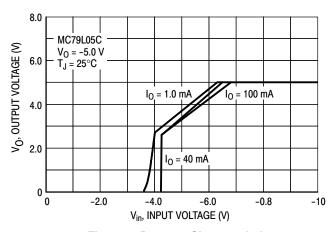


Figure 4. Dropout Characteristics

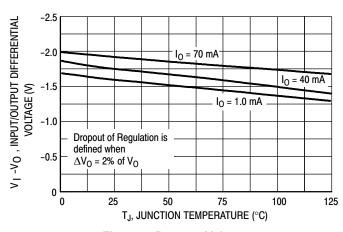


Figure 5. Dropout Voltage versus Junction Temperature

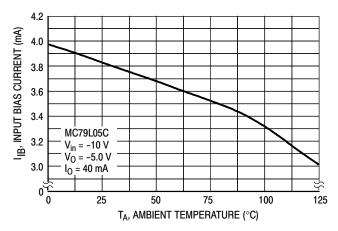


Figure 6. Input Bias Current versus Ambient Temperature

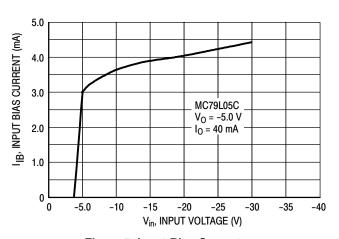


Figure 7. Input Bias Current versus Input Voltage

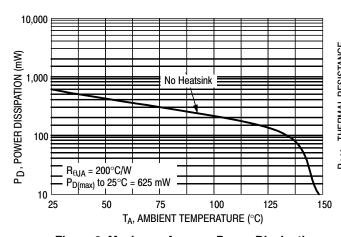


Figure 8. Maximum Average Power Dissipation versus Ambient Temperature (TO-92)

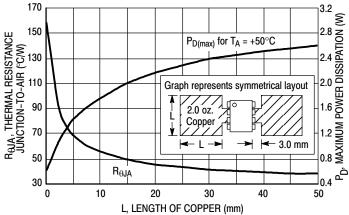


Figure 9. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

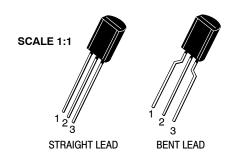
ORDERING INFORMATION

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L05ABDG	-5.0 V	TJ = -40° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ABPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACDG		TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACPRMG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L05ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L12ABDG	-12 V	TJ = -40° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L12ABPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L12ACDG	-12 V	TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L12ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L12ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box

ORDERING INFORMATION (continued)

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L15ABDG	-15 V	TJ = -40° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ABPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L15ACDG		TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L15ACPREG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L15ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L18ABPRPG	-18 V	TJ = -40° to +125°C	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L18ACPG		TJ = 0° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ABPG	-24 V	TJ = -40° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ACPG		TJ = 0° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ACPRMG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L24ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box

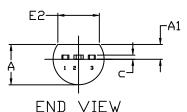
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

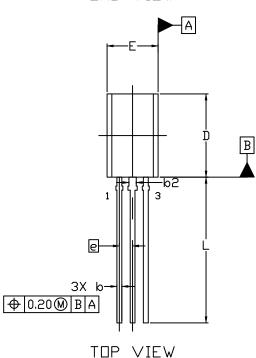


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

STRAIGHT LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Δ	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
Ø	0.38	0.465	0.55		
ρQ	0.62	0.70	0.78		
C	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E2	3.90				
е	1.27 BSC				
L	13.80	14.00	14.20		

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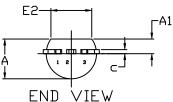
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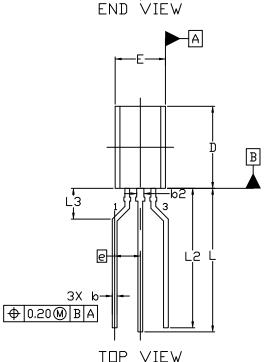


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Α	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
b	0.38	0.465	0.55		
b2	0.62	0.70	0.78		
С	0.35	0.40	0.45		
D	7.85	8.00	8.15		
Е	4.75	4.90	5.05		
E2	3.90				
O.	2.50 BSC				
L	13.80	14.00	14.20		
L2	13.20	13.60	14.00		
L3	·	3.00 REF	·		

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CASE 29-10 ISSUE D

DATE 05 MAR 2021

2.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN	2.	BASE 1 EMITTER BASE 2		CATHODE GATE ANODE
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2		EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1
2.	ANODE	DINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	PIN 1. 2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.		PIN 1. 2.		PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	V _{CC}		MT	PIN 1. 2.		PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.80	5.00	0.189	0.197		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.053	0.069		
D	0.33	0.51	0.013	0.020		
G	1.27	7 BSC	0.050 BSC			
Н	0.10	0.25	0.004	0.010		
J	0.19	0.25	0.007	0.010		
K	0.40	1.27	0.016	0.050		
М	0 °	8 °	0 °	8 °		
N	0.25	0.50	0.010	0.020		
S	5.80	6.20	0.228	0.244		

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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STYLE 4: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 2 4. ANODE 5. ANODE #2 6. ANODE #2 7. ANODE #1 8. COMMON CATHODE
STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 STAGE Vd 7. EMITTER, #1 AGE Vd 8. COLLECTOR, #1
STYLE 12: 1 PIN 1. SOURCE 2 SOURCE 2 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COMMON 6. COLLECTOR, DIE #2 6. COMMON 7. COLLECTOR, DIE #1 6. COMMON 8. COLLECTOR, DIE #1
STYLE 20: 1 PIN 1. SOURCE (N) 2. GATE (N) 2 3. SOURCE (P) 4. GATE (P) 5. DRAIN 2 6. DRAIN 7. DRAIN 1 8. DRAIN
STYLE 24: PIN 1. BASE N ANODE/GND 2. EMITTER N ANODE/GND 3. COLLECTOR/ANODE UT 5. CATHODE N ANODE/GND 6. CATHODE N ANODE/GND 7. COLLECTOR/ANODE UT 8. COLLECTOR/ANODE
STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND E 5. V_MON E 6. VBULK E 7. VBULK 8. VIN

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